

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (L<sup>2</sup>-π-MOSV)

# 2SK2614

Chopper Regulator, DC/DC Converter and Motor Drive Applications

- 4 V gate drive
- Low drain-source ON-resistance :  $R_{DS(ON)} = 0.032 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 13S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 50 V$ )
- Enhancement mode :  $V_{th} = 0.8\sim 2.0 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	50	V	
Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)	$V_{DGR}$	50	V	
Gate-source voltage	$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	$I_D$	20	A
	Pulse (Note 1)	$I_{DP}$	50	A
Drain power dissipation (T <sub>c</sub> = 25°C)	$P_D$	40	W	
Channel temperature	$T_{ch}$	150	°C	
Storage temperature range	$T_{stg}$	-55~150	°C	

Note 1: Ensure that the channel temperature does not exceed 150°C.

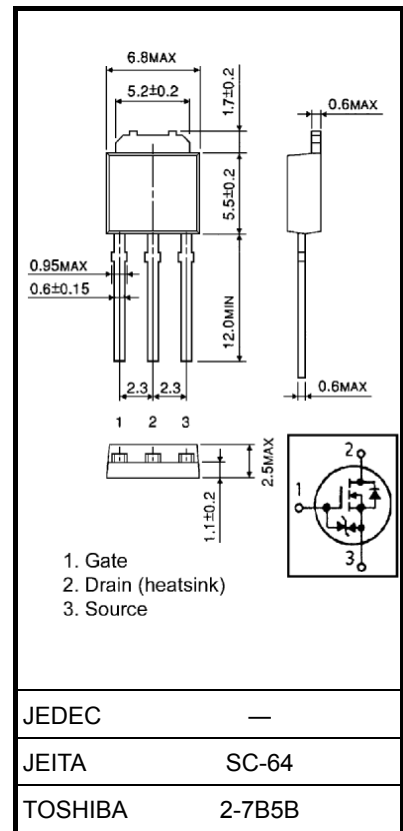
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

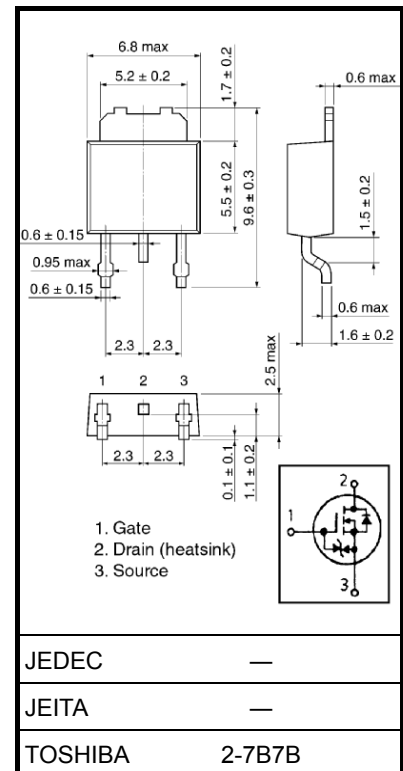
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	3.125	°C / W
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	°C / W

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.36 g (typ.)



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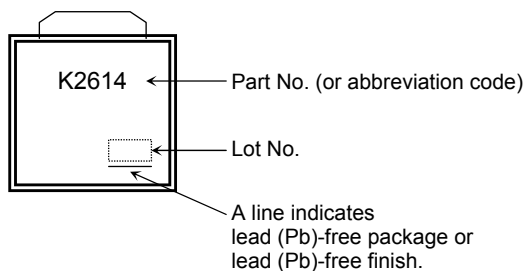
## Electrical Characteristics (Ta = 25°C)

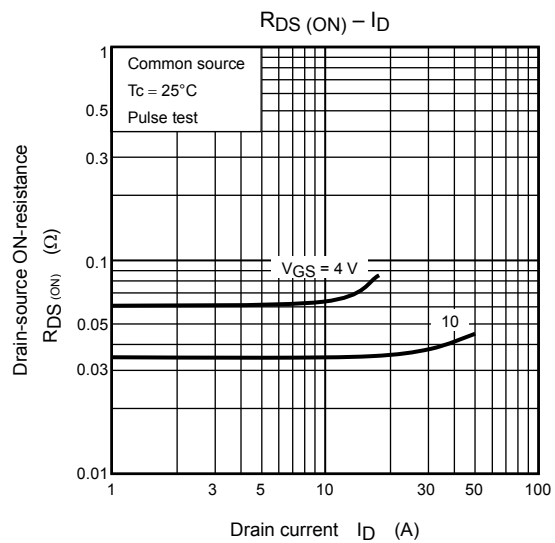
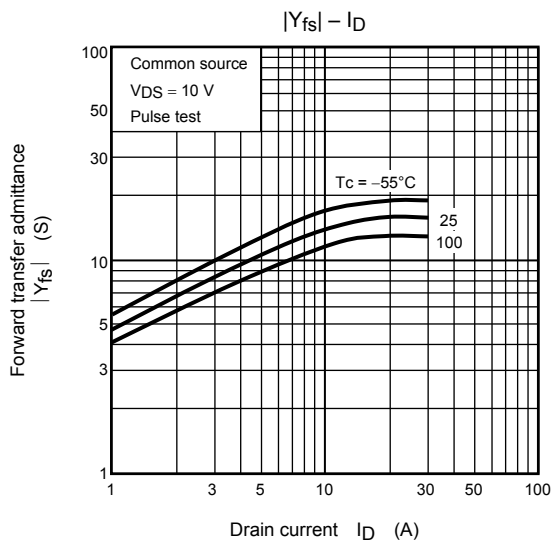
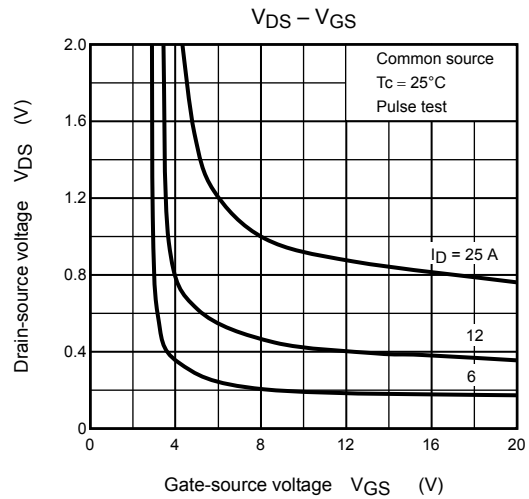
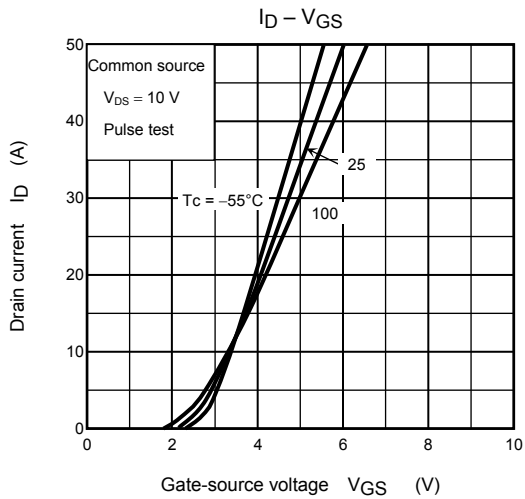
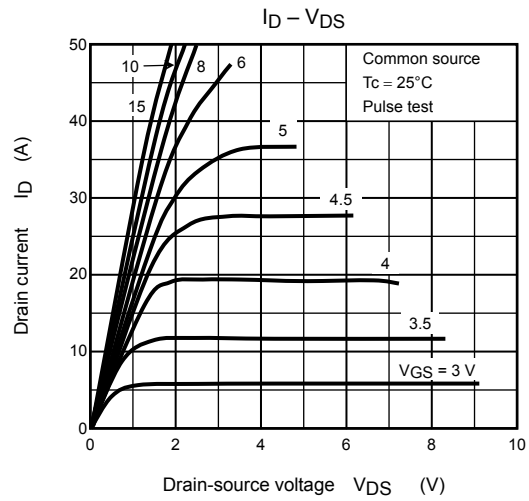
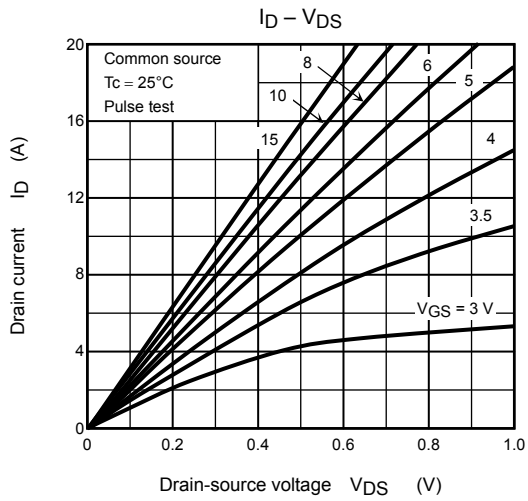
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cutoff current		$I_{DSS}$	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	50	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.8	—	2.0	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{DS} = 4\text{ V}, I_D = 5\text{ A}$	—	0.055	0.08	$\Omega$
			$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$	—	0.032	0.046	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$	7	13	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	900	—	pF
Reverse transfer capacitance		$C_{rss}$		—	130	—	
Output capacitance		$C_{oss}$		—	370	—	
Switching time	Rise time	$t_r$		—	15	—	ns
	Turn-on time	$t_{on}$		—	25	—	
	Fall time	$t_f$		—	30	—	
	Turn-off time	$t_{off}$		—	100	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	—	25	—	nC
Gate-source charge		$Q_{gs}$		—	19	—	
Gate-drain ("Miller") charge		$Q_{gd}$		—	6	—	

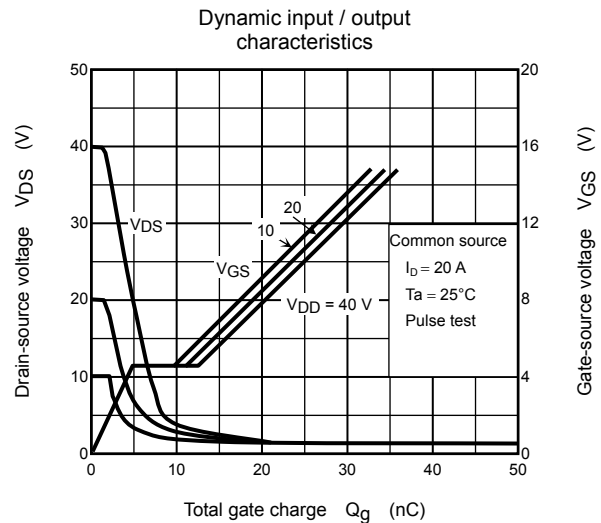
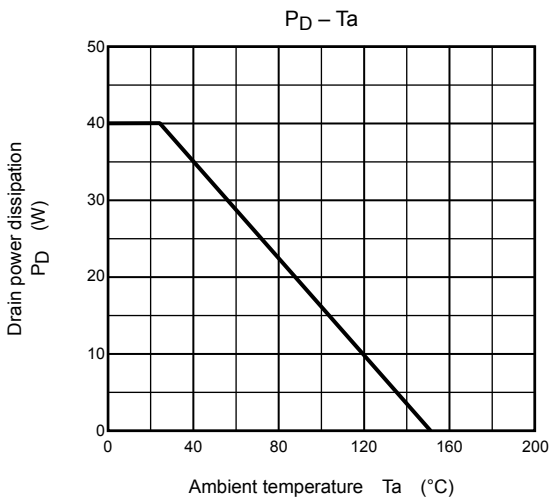
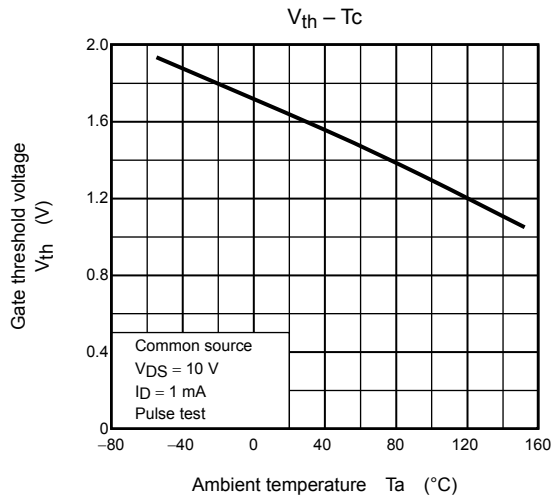
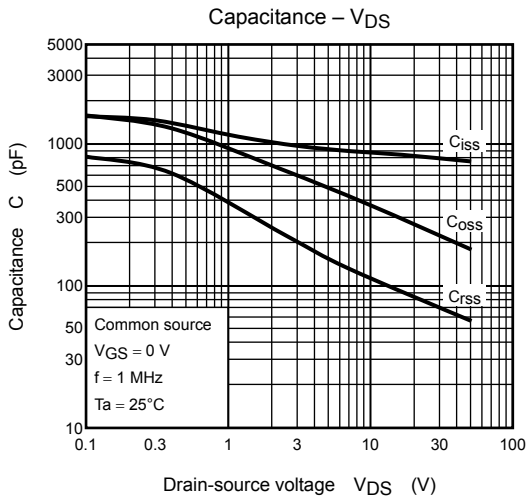
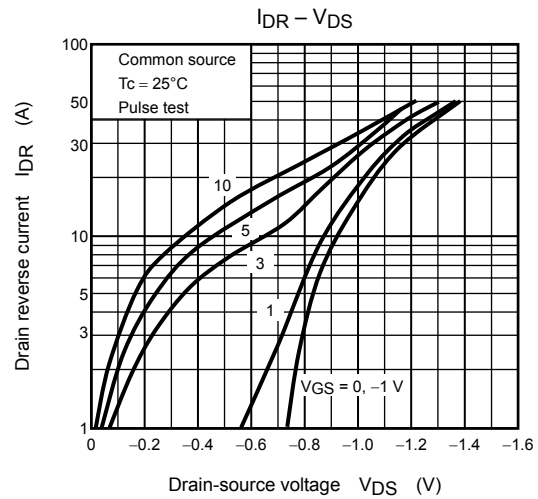
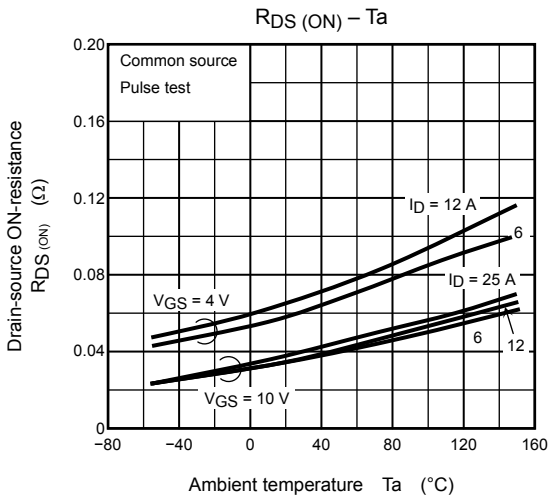
## Source-Drain Ratings and Characteristics (Ta = 25°C)

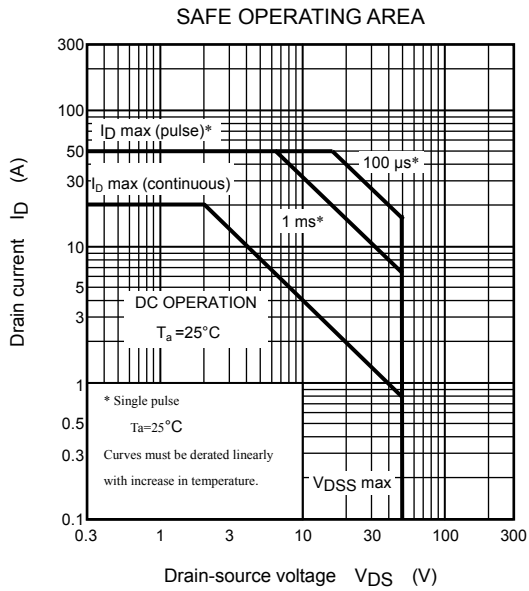
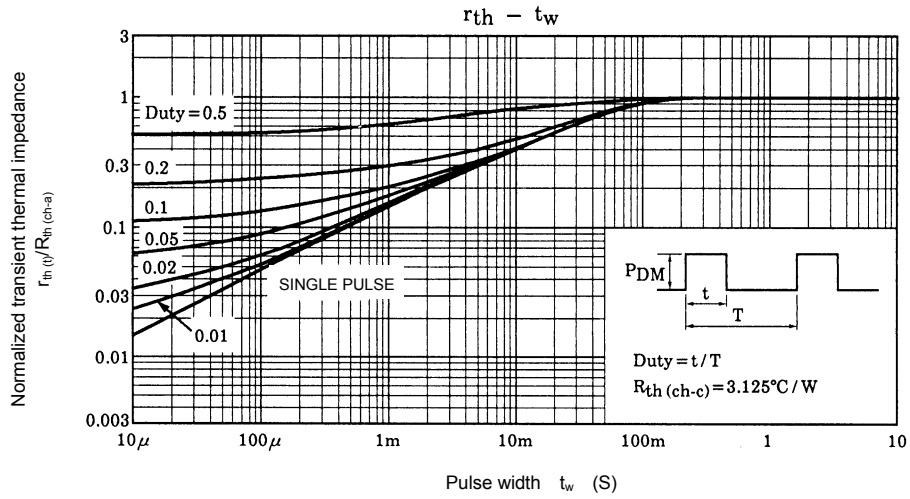
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	20	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	50	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 20\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 20\text{ A}, V_{GS} = 0\text{ V}, dI_{DR} / dt = 50\text{ A} / \mu\text{s}$	—	60	—	ns
Reverse recovery charge	$Q_{rr}$		—	45	—	$\mu\text{C}$

## Marking









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